



GRAPHENE AND 2DM VIRTUAL CONFERENCE & EXPO

Accurate many-body calculation of electronic and optical band gap of bulk hexagonal boron nitride

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Introduction

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Recent interest in two-dimensional (2D) materials has re-initiated intensive discussion on bulk layered materials' electronic and optical properties. The debate concerning the band gap of bulk hexagonal boron nitride (h-BN), its nature, and excitonic properties was re-opened by recent experiments^{1,2}. While graphite (and its 2D analog called graphene) is a zero band gap semi-metal, h-BN is a wide gap semiconductor with very high thermal and chemical stability suitable in devices operating under extreme conditions. Experimental estimation of the bulk h-BN band gap has been a long-debated issue, and different experiments have varied. The nature of the band gap was controversial too. Still, this recent experimental studies brought a turning point in this consensus and showed the band gap's nature as indirect and reported very accurate values of the electronic and optical band gaps.

Methods

Experimental lattice constants of a = 2.502 Å and c = 6.617 Å¹ was used. The Vienna *ab initio* simulation package (VASP)³ implementing projector augmented-wave (PAW) method, GW set of PAWs, and cut-off energy $E_{cut} = 500 \text{ eV}$ are used in all calculations (2s1p electrons are explicitly treated). We use GW⁴ approximation with input orbitals from DFT and Perdew,



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Burke and Ernzerhof (PBE) functional⁵ for electronic structure calculations. The break condition for the electronic step is an energy difference of 1 x 10⁻⁶ eV. Excitonic effects are accounted for by the Bethe–Salpeter equation⁶.

Benchmark GW and BSE study of h-BN band gaps

Results

Simple scissor approximation of h-BN band structures







Figure 4. Electronic band structure of h-BN (AA`) from G₀W₀ calculation (black

Figure 1. Convergence of h-BN (AA`) band gaps E_{nan} (indirect, direct in M, optical) and exciton binding energy E_{h}^{exc} $= E_{gap}^{M} - E_{b}^{opt}$ in eV. A) With respect to GW number of bands $N_{_{\rm B}}$ and energy cut-off E cut (indicated in the legend, in eV); B) With respect to number of iteration i in G_iW_0 and G_iW_1 calculations. 12 x 12 x 4 k-grid was used. Green points are experimental values.^{1,2}

Table 1. Comparison of calculated gap values with experimental values.

	$E_{ m gap}^{ m indir}$	$E_{ m gap}^{M/K}$	$E_{ m gap}^{ m opt}$	$E_{\rm b}^{ m exc}$
Calc. AA'	6.08	6.53	5.71	0.82
Calc. AB	6.17	6.39	5.61	0.78
$Exp.^{1,2}$	6.08	6.42	5.69	0.73

Figure 2. Conduction (top) and valence (bottom) bands of h-BN obtained from G_0W_0 calculation as cuts through the plane G–M–K in the first Brillouin zone.



Figure 3. Change in h-BN band gaps E_{gab} (indirect, direct in M, optical) and exciton binding energy $E_{b}^{exc} = E_{gab}^{M} - E_{b}^{opt}$ in eV with respect to c lattice parameter. Two h-BN stacking configurations are considered, AA` and AB.

triangles) and electron-hole contributions to first excitonic peak from BSE calculation (represented by radius of colored circles). Scissor corrected DFT (PBE) band structure, DFT+ Δ (blue lines), seems a very good approximation to the G₀W₀ band structure. Fermi energy is set as zero.



Conclusions

Our carefully converged results reveal h-BN as an indirect material (indirect gap \approx 6.1 eV) with a huge excitonic effect ($\approx 0.8 \text{ eV}$) in agreement with recent revolutionary experiments^{1,2}. Variability of previous theoretical predictions and our convergence tests indicate that many-body methods should be used carefully, and numerical convergence should always be performed. On the other hand, based on benchmark G₀W₀ results, we suggest a computationally cheap scissor corrected DFT approach providing band structure comparable with the G_0W_0 band structure. Time-dependent DFT with a suitable exchangecorrelation kernel can provide absorption spectra that mimic the full G_0W_0 +BSE spectra.

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Figure 5. Optical absorption spectra (imaginary part of dielectric function) of h-BN (AA`) using various approximate methods and the reference and the reference G_0W_0 +BSE curve (blue line). The electronhole ladder diagrams in present TD-DFT calculations are approximated by the exact exchange (EEX) and different EEX/GGA ratio is evaluated (and labeled by the EEX part as TD_{FEX} -PBE+ Δ). We achieve surprisingly good approximation with EEX/GGA ratio of 0.3/0.7.

